



### IPP110N20N3 G Information



For Reference Only

**Part Number** IPP110N20N3 G **Manufacturer** Infineon Technologies

**Category** Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 200V 88A TO220-3

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# IPP110N20N3 G Specifications

Manufacturer Part Number         IPP110N20N3 G           Manufacturer         Infineon Technologies           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         OptiMOS?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         200V           Current - Continuous Drain (Id) @ 25°C         88A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 270µA           Gate Charge (Qg) (Max) @ Vgs         87nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         7100pF @ 100V           Vgs (Max)         2 ± 20V           FET Feature         -           Power Dissipation (Max)         300W (Tc)           Rds On (Max) @ Id, Vgs         11 mOhm @ 88A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         PG-TO-220-3           Package / Case         TO-220-3		
Category         Discrete Semiconductor Products           Package         TO-220-3           Series         OptiMOS?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         200V           Current - Continuous Drain (Id) @ 25°C         88A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 270µA           Gate Charge (Qg) (Max) @ Vgs         87nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         7100pF @ 100V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         300W (Tc)           Rds On (Max) @ Id, Vgs         11 mOhm @ 88A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         PG-TO-220-3           Package / Case         TO-220-3	Manufacturer Part Number	IPP110N20N3 G
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C88A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 270μAGate Charge (Qg) (Max) @ Vgs87nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7100pF @ 100VVgs (Max)±20VFET Feature-Power Dissipation (Max)300W (Tc)Rds On (Max) @ Id, Vgs11 mOhm @ 88A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO-220-3Package / CaseTO-220-3	Package	TO-220-3
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 88A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 270μA Gate Charge (Qg) (Max) @ Vgs 87nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7100pF @ 100V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11 mOhm @ 88A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case  MOSFET (Metal Oxide) 200V  88A (Tc) 88A (Tc)  10V  4V @ 270μA 4V @ 270μA 57100pF @ 100V 4V @ 270μA 57100pF @ 100V 4V @ 270μA 57100pF @ 100V	Series	OptiMOS?
Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C88A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 270μAGate Charge (Qg) (Max) @ Vgs87nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7100pF @ 100VVgs (Max)±20VFET Feature-Power Dissipation (Max)300W (Tc)Rds On (Max) @ Id, Vgs11 mOhm @ 88A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO-220-3Package / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C  Bask (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Rnput Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  11 mOhm @ 88A, 10V  Operating Temperature  Supplier Device Package  PG-TO-220-3  Package / Case  88A (Tc)  90V  7100pF @ 100V  7100pF @ 10	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 270μAGate Charge (Qg) (Max) @ Vgs87nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7100pF @ 100VVgs (Max)±20VFET Feature-Power Dissipation (Max)300W (Tc)Rds On (Max) @ Id, Vgs11 mOhm @ 88A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO-220-3Package / CaseTO-220-3	Drain to Source Voltage (Vdss)	200V
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Gate Charge (Qg) (Max) @ Vgs       87nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       7100pF @ 100V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       300W (Tc)         Rds On (Max) @ Id, Vgs       11 mOhm @ 88A, 10V         Operating Temperature       -55°C ~ 175°C (TJ)         Mounting Type       Through Hole         Supplier Device Package       PG-TO-220-3         Package / Case       TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
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Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  11 mOhm @ 88A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PG-TO-220-3  Package / Case  TO-220-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 11 mOhm @ 88A, 10V  Operating Temperature -55°C ~ 175°C (TJ)  Mounting Type Through Hole  Supplier Device Package PG-TO-220-3  Package / Case TO-220-3	FET Feature	-
Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PG-TO-220-3  Package / Case  TO-220-3	Power Dissipation (Max)	300W (Tc)
Mounting Type Through Hole Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	11 mOhm @ 88A, 10V
Supplier Device Package PG-TO-220-3 Package / Case TO-220-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	PG-TO-220-3
Report errors?	Package / Case	TO-220-3
		Report errors?

### IPP110N20N3 G Guarantees



### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### **IPP110N20N3 G Payment Methods**



















## IPP110N20N3 G Shipping Methods













If you have any question about IPP110N20N3 G, please do not hesitate to contact us!

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